



DMP3125L

#### 30V P-CHANNEL ENHANCEMENT MODE MOSFET

## **Product Summary**

BV <sub>DSS</sub>	RDS(ON) max	I <sub>D</sub> T <sub>A</sub> = +25°C
-30V	$95m\Omega @ V_{GS} = -10V$	-2.5A
-30 V	145mΩ @ $V_{GS} = -4.5V$	-2.0A

## **Description and Applications**

This new generation MOSFET is designed to minimize the on-state resistance ( $R_{DS(ON)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Boost Switch
- Power Management Functions
- Analog Switch
- Load Switch

### **Features and Benefits**

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

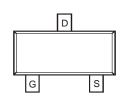
### **Mechanical Data**

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
   Solderable per MIL-STD-202, Method 208 (3)
- Terminals Connections: See Diagram Below
- Weight: 0.009 grams (Approximate)

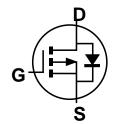




Top View



SOT23



**Equivalent Circuit** 

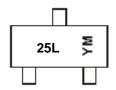
## Ordering Information (Note 4)

Part Number	Case	Packaging
DMP3125L-7	SOT23	3,000/Tape & Reel
DMP3125L-13	SOT23	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

## **Marking Information**



25L = Product Type Marking Code YM = Date Code Marking Y or Y = Year (ex: E = 2017) M = Month (ex: 9 = September)

Date Code Key

Year	2017	2018	20	019	2020	2021		2022	2023	20:	24	2025
Code	Е	F		G	Н	1		J	K	L		М
Month	Jan	Feb	Mar	Apr	May	Jun	Ju	ıl Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



# 

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	$V_{DSS}$	-30	V
Gate-Source Voltage	$V_{GSS}$	±20	V
Continuous Drain Current (Note 6) V <sub>GS</sub> = -10V	I <sub>D</sub>	-2.5 -2.0	А
Maximum Continuous Body Diode Forward Current (	Is	-1.5	Α
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	-10	Α

## Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

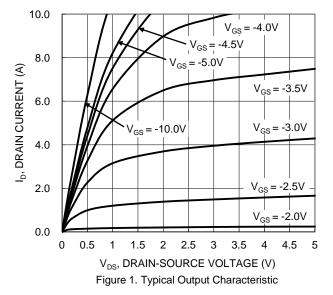
Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		$P_D$	0.65	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{ heta JA}$	191	°C/W
Total Power Dissipation (Note 6)		P <sub>D</sub>	1.2	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{ heta JA}$	103	°C/W
Operating and Storage Temperature Range		$T_{J}$ , $T_{STG}$	-55 to +150	°C

## Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-30	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>			-1	μA	V <sub>DS</sub> = -30V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	_		±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-1.0	-	-2.1	٧	$V_{DS} = V_{GS}$ , $I_D = -250\mu A$
Static Drain-Source On-Resistance	D	1	76	95	mΩ	$V_{GS} = -10V, I_D = -3.8A$
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	108	145	11177	V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -3.0A
Diode Forward Voltage	$V_{SD}$	_	-0.85	-1.2	V	$V_{GS} = 0V, I_S = -2.7A$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C <sub>iss</sub>	1	254	-	pF	
Output Capacitance	Coss	1	14	1	pF	$V_{DS} = -25V, V_{GS} = 0V$ f = 1.0MHz
Reverse Transfer Capacitance	C <sub>rss</sub>	1	7	1	pF	1 - 1.51/11/2
Gate Resistance	$R_g$	1	54	1	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$
Total Gate Charge	$Q_g$	_	3.1	_	nC	
Gate-Source Charge	$Q_{gs}$	_	0.8	_	nC	$V_{GS} = -4.5V, V_{DS} = -15V$ $I_{D} = -3.8A$
Gate-Drain Charge	$Q_{gd}$	_	1.4	_	nC	10 = 3.0A
Turn-On Delay Time	t <sub>D(ON)</sub>	_	3.5	_	ns	
Turn-On Rise Time	t <sub>R</sub>	_	6.3	_	ns	V <sub>DS</sub> = -15V, V <sub>GS</sub> = -10V,
Turn-Off Delay Time	t <sub>D(OFF)</sub>	1	21.8		ns	$R_G = 6.0\Omega, I_D = -1A$
Turn-Off Fall Time	t <sub>F</sub>	_	13.1	_	ns	
Reverse Recovery Time	t <sub>RR</sub>	_	9.6		ns	I <sub>F</sub> = -1.0A, di/dt = 100A/μs
Reverse Recovery Charge	$Q_{RR}$	_	2.4	_	nC	I <sub>F</sub> = -1.0A, di/dt = 100A/μs

- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
   Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
   Short duration pulse test used to minimize self-heating effect.
   Guaranteed by design. Not subject to product testing.





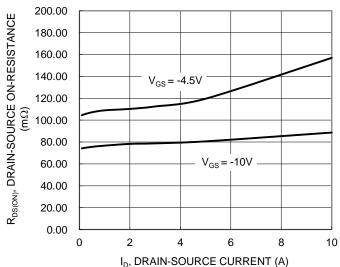
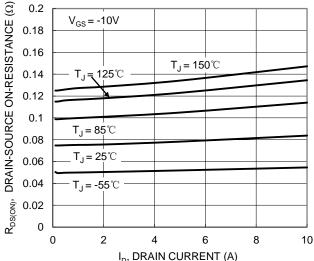
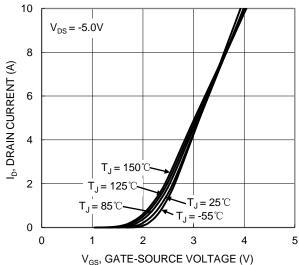


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage



I<sub>D</sub>, DRAIN CURRENT (A) Figure 5. Typical On-Resistance vs. Drain Current and Temperature



V<sub>GS</sub>, GATE-SOURCE VOLTAGE (V)
Figure 2. Typical Transfer Characteristic

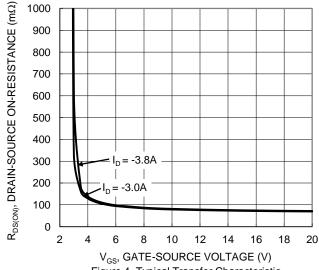
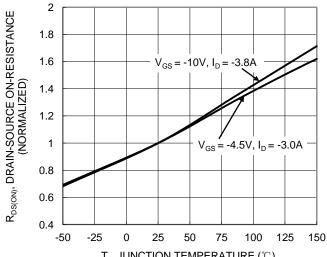


Figure 4. Typical Transfer Characteristic



 $\mathsf{T_J},\mathsf{JUNCTION}$  TEMPERATURE (°C) Figure 6. On-Resistance Variation with Temperature



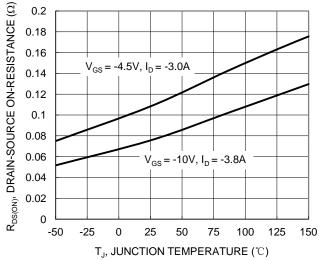
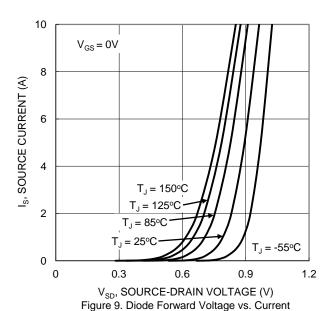


Figure 7. On-Resistance Variation with Temperature



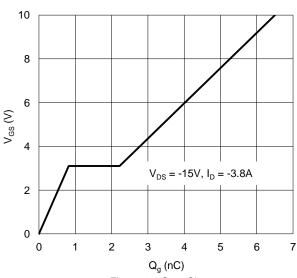


Figure 11. Gate Charge

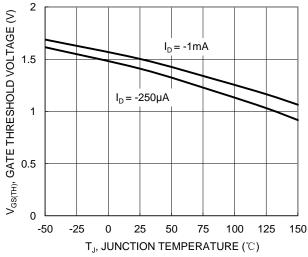


Figure 8. Gate Threshold Variation vs. Junction Temperature

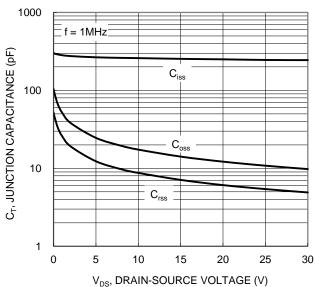


Figure 10. Typical Junction Capacitance

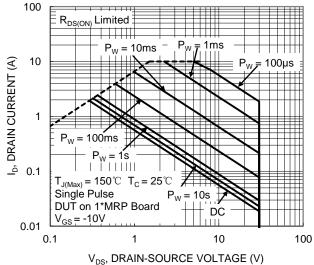


Figure 12. SOA, Safe Operation Area



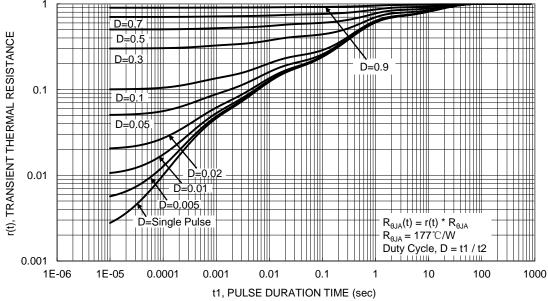


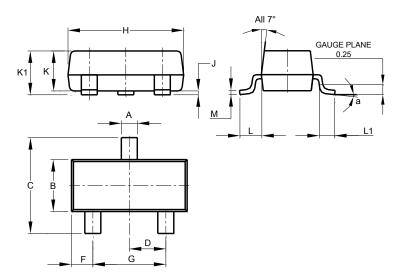
Figure 13. Transient Thermal Resistance



## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### SOT23

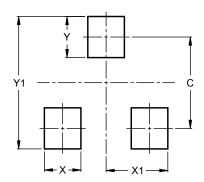


SOT23							
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
C	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
J	0.013	0.10	0.05				
K	0.890	1.00	0.975				
K1	0.903	1.10	1.025				
L	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
М	0.085	0.150	0.110				
а	0°	8°					
All Dimensions in mm							

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### SOT23



Dimensions	Value (in mm)
C	2.0
Х	0.8
X1	1.35
Υ	0.9
Y1	2.9



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